TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

# SSM3K17FU

# High Speed Switching Applications Analog Switch Applications

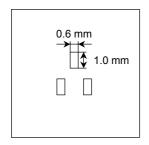
- · Suitable for high-density mounting due to compact package
- High drain-source voltage
- High speed switching

#### **Maximum Ratings (Ta = 25°C)**

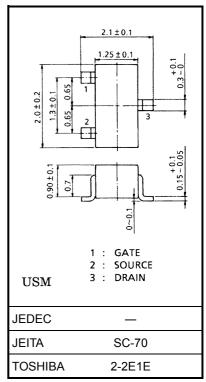
Characteristics		Symbol	Rating	Unit	
Drain-Source voltage		$V_{DS}$	50	V	
Gate-Source voltage		$V_{GSS}$	±7	V	
Drain current	DC	I <sub>D</sub>	100	mA	
	Pulse	I <sub>DP</sub>	200		
Drain power dissipation (Ta = 25°C)		P <sub>D</sub> (Note)	150	mW	
Channel temperature		T <sub>ch</sub>	150	°C	
Storage temperature range		T <sub>stg</sub>	-55~150	°C	

Note: Mounted on FR4 board

(25.4 mm × 25.4 mm × 1.6 t, Cu Pad: 0.6 mm<sup>2</sup> × 3)



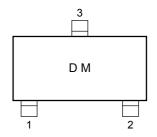
#### Unit: mm

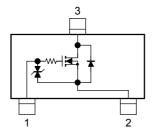


Weight: 6 mg (typ.)

#### Marking

### **Equivalent Circuit**





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This transistor is a electrostatic sensitive device. Please handle with caution.

## **Electrical Characteristics (Ta = 25°C)**

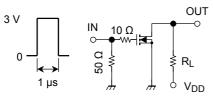
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	$V_{GS} = \pm 7 \text{ V}, V_{DS} = 0$	_	_	±5	μΑ
Drain-Source breakdown voltage		V (BR) DSS	I <sub>D</sub> = 0.1 mA, V <sub>GS</sub> = 0	50	_	_	V
Drain cut-off current		I <sub>DSS</sub>	V <sub>DS</sub> = 50 V, V <sub>GS</sub> = 0	_	_	1	μA
Gate threshold volt	age	$V_{th}$	$V_{DS} = 3 \text{ V}, I_{D} = 1 \mu A$	0.9	_	1.5	V
Forward transfer admittance		Y <sub>fs</sub>	V <sub>DS</sub> = 3 V, I <sub>D</sub> = 10 mA	20	40	_	mS
Drain-Source ON resistance		R <sub>DS</sub> (ON)	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 4 V	_	12	20	Ω
			$I_D$ = 10 mA, $V_{GS}$ = 2.5 V	_	22	40	
Input capacitance		C <sub>iss</sub>	V <sub>DS</sub> = 3 V, V <sub>GS</sub> = 0, f = 1 MHz	_	7	_	pF
Reverse transfer capacitance		C <sub>rss</sub>	V <sub>DS</sub> = 3 V, V <sub>GS</sub> = 0, f = 1 MHz	_	3	_	pF
Output capacitance		Coss	V <sub>DS</sub> = 3 V, V <sub>GS</sub> = 0, f = 1 MHz	_	7	_	pF
Switching time	Turn-on time	t <sub>on</sub>	$V_{DD}$ = 3 V, $I_{D}$ = 20 mA, $V_{GS}$ = 0~3 V, $R_{G}$ = 10 $\Omega$ , $R_{L}$ = 150 $\Omega$	_	100	_	ns
	Turn-off time	t <sub>off</sub>		_	40	_	

# **Switching Time Test Circuit**

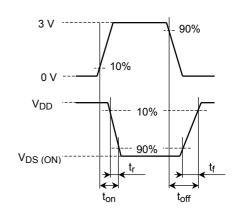
(a) Test circuit

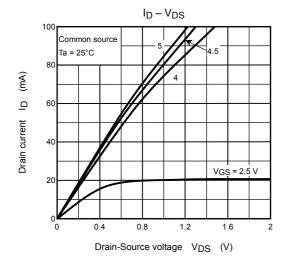
(b) V<sub>IN</sub>

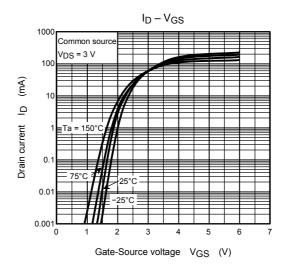
(c) V<sub>OUT</sub>

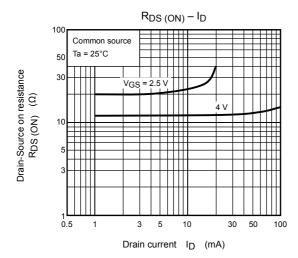


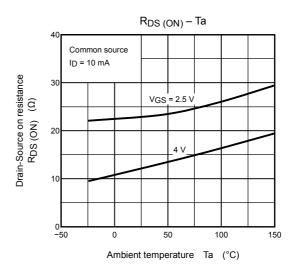
$$\begin{split} &V_{DD}=3 \text{ V}\\ &\text{Duty} \leq 1\%\\ &V_{IN}\text{: }t_{r},\,t_{f} < 5 \text{ ns}\\ &(Z_{out}=50 \text{ }\Omega)\\ &\text{Common source}\\ &\text{Ta}=25^{\circ}\text{C} \end{split}$$

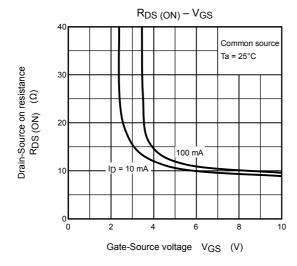


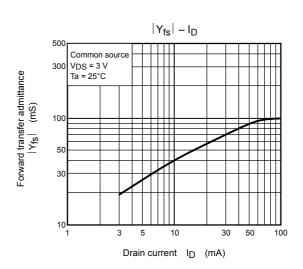




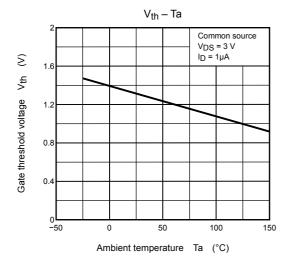


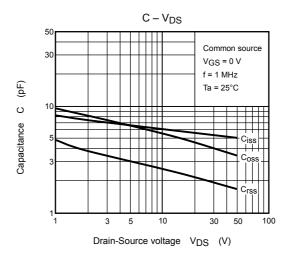


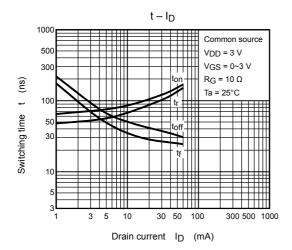


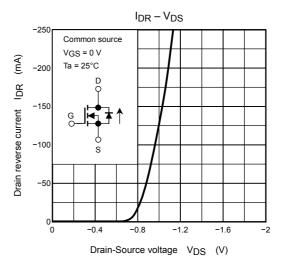


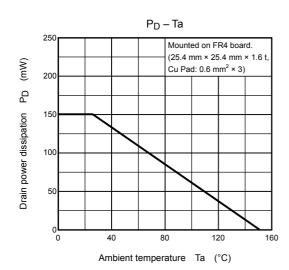
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